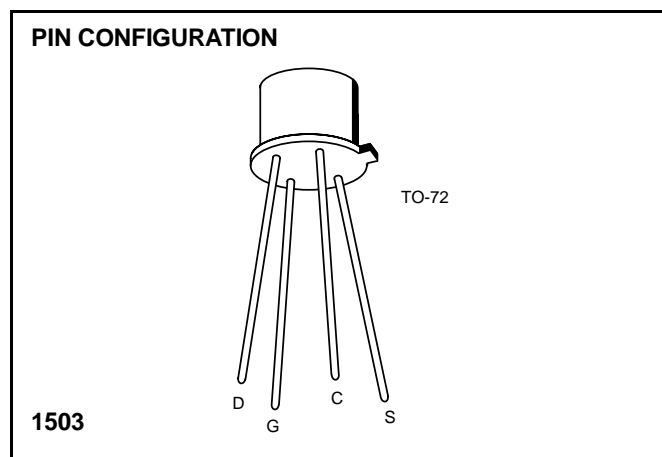


FEATURES

- Low ON Resistance
- Low Capacitance
- High Gain
- P-Channel Complement to 2N4341



ABSOLUTE MAXIMUM RATINGS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Drain-Source Voltage	25V
Drain-Gate Voltage	30V
Gate-Source Voltage	$\pm 30\text{V}$
Drain Current	30mA
Storage Temperature Range	-65°C to $+200^\circ\text{C}$
Operating Temperature Range	-55°C to $+150^\circ\text{C}$
Lead Temperature (Soldering, 10sec)	$+300^\circ\text{C}$
Power Dissipation	300mW
Derate above 25°C	$1.7\text{mW}/^\circ\text{C}$

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

Part	Package	Temperature Range
2N4352	Hermetic TO-72	-55°C to $+150^\circ\text{C}$
X2N4352	Sorted Chips in Carriers	-55°C to $+150^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
$V_{(BR)DSX}$	Drain-Source Breakdown Voltage	-25		Vdc	$I_D = -10\mu\text{A}$, $V_{GS} = 0$
I_{DSS}	Zero-Gate-Voltage Drain Current		-10 -10	nAdc μAdc	$V_{DS} = -10\text{V}$, $V_{GS} = 0$, $T_A = 25^\circ\text{C}$ $V_{DS} = -10\text{V}$, $V_{GS} = 0$, $T_A = 150^\circ\text{C}$
I_{GSS}	Gate Reverse Current		± 10	pA	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0$
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	-5.0	Vdc	$V_{DS} = -10\text{V}$, $I_D = -10\mu\text{A}$
$V_{DS(on)}$	Drain-Source On-Voltage		-1.0	V	$I_D = -2\text{mA}$, $V_{GS} = -10\text{V}$
$I_{D(on)}$	On-State Drain Current	-3.0		mA	$V_{GS} = -10\text{V}$, $V_{DS} = -10\text{V}$
$r_{DS(on)}$	Drain-Source Resistance		600	ohms	$V_{GS} = -10\text{V}$, $I_D = 0$, $f = 1.0\text{kHz}$
$ y_{fs} $	Forward Transfer Admittance	1000		μmho	$V_{DS} = -10\text{V}$, $I_D = 2.0\text{mA}$, $f = 1.0\text{kHz}$
C_{iss}	Input Capacitance		5.0	pF	$V_{DS} = -10\text{V}$, $V_{GS} = 0$, $f = 140\text{MHz}$
C_{rss}	Reverse Transfer Capacitance		1.3		$V_{DS} = 0$, $V_{GS} = 0$, $f = 140\text{MHz}$
$C_{d(sub)}$	Drain-Substrate Capacitance		5.0		$V_{D(sub)} = -10\text{V}$, $f = 140\text{kHz}$
t_{d1}	Turn-On Delay		45	ns	$I_D = -2.0\text{mAdc}$, $V_{DS} = -10\text{Vdc}$ $V_{GS} = -10\text{V}$
t_r	Rise Time		65		
t_{d2}	Turn-Off Delay		60		
t_f	Fall Time		100		